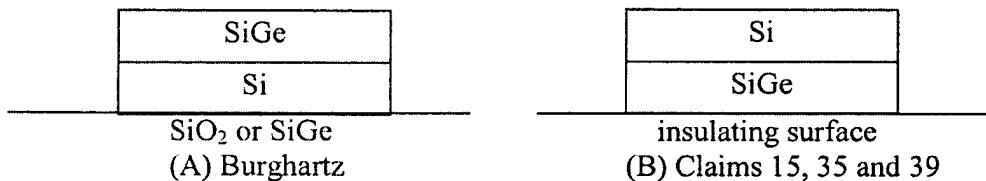


second amorphous semiconductor films. The Examiner refers to Burghartz to remedy this deficiency.

Burghartz, however, does not describe or suggest forming a first amorphous semiconductor film that includes silicon and germanium on an insulating surface and then forming, on the first amorphous semiconductor film, a second amorphous semiconductor film that includes silicon. Rather, Burghartz describes the exact opposite. In particular, Burghartz describes depositing a thin amorphous silicon layer 106 on a silicon dioxide layer 114 and then depositing a silicon germanium layer 102 on top of the silicon layer 106. See Fig. 1; and steps 406 and 408 of Fig. 4 of Burghartz. This distinction is illustrated in the figure below:



Burghartz notes that an advantage is attained by depositing the thin amorphous silicon layer 106 prior to depositing the silicon germanium layer 102 in that the thin amorphous silicon layer 106 is thereby able to function as a seed layer for the subsequent silicon germanium layer deposition. See col. 8, lines 60-63. Accordingly, a person of ordinary skill in the art would not have been led to reverse the order of these layers because such a reversal would prevent the advantageous use of the thin amorphous silicon layer 106 as a seed layer for formation of the silicon germanium layer 102.

For at least these reasons, applicants request reconsideration and withdrawal of the rejections of claims 15, 35 and 39, and their dependent claims.

Each of independent claims 36 and 40 recites, among other features, “forming a first amorphous semiconductor film comprising silicon and germanium on the gate insulating film” (emphasis added) and “forming a second amorphous semiconductor film comprising silicon on the first amorphous semiconductor film” (emphasis added). Independent claim 16 recites, among other features, “forming a first amorphous semiconductor film comprising silicon and an

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element having a larger atomic radius than silicon on an insulating surface" (emphasis added) and "forming a second amorphous semiconductor film on the first amorphous semiconductor film" (emphasis added). For at least the reasons described above, applicants request reconsideration and withdrawal of the rejections of claims 16, 36 and 40, and their dependent claims, because neither claims 1-127 of the '956 patent, claims 1-70 of the '453 patent, claims 1-70 of the '943 patent, Burghartz nor any proper combination thereof describes or suggests forming the recited two amorphous semiconductor films.

Applicants submit that all claims are in condition for allowance.

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Respectfully submitted,



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